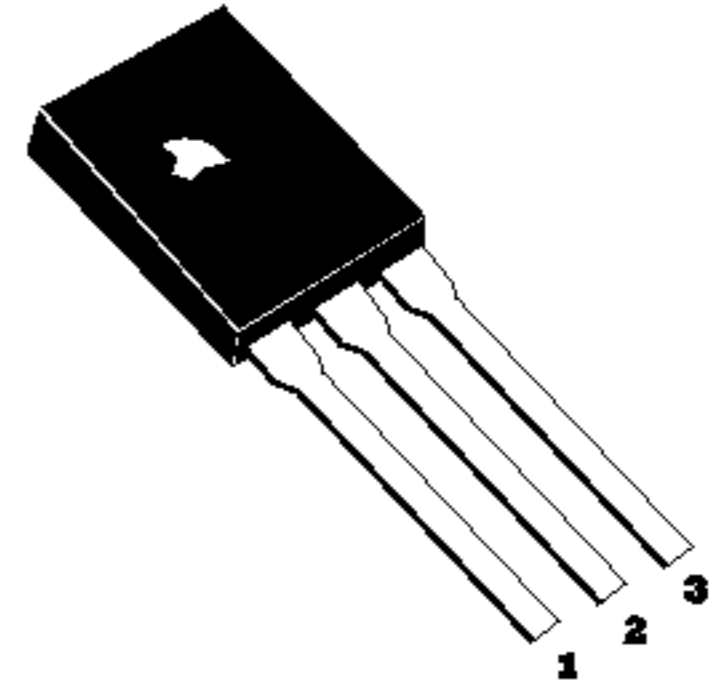




**HIGH VOLTAGE TRANSISTOR**

- \* Collector-Emitter Voltage  $V_{ce0}=400V$
- \* Collector Dissipation  $P_c(\text{Max})=1W$  ( $T_a=25^\circ C$ )

Package: TO-126



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**ABSOLUTE MAXIMUM RATINGS at  $T_{amb}=25^\circ C$**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{cbo}$	500	V
Collector-Emitter Voltage	$V_{ceo}$	400	V
Emitter-Base Voltage	$V_{ebo}$	8	V
Collector Current	$I_c$	500	mA
Collector Dissipation	$P_c$	1	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55~150	$^\circ C$

PIN:	1	2	3
STYLE			
NO.1	E	C	B

**ELECTRICAL CHARACTERISTICS at  $T_{amb}=25^\circ C$**

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	$BV_{cbo}$	500			V	$I_c=100\mu A$ $I_e=0$
Collector-Emitter Breakdown Voltage	$BV_{ceo}$	400			V	$I_c=1mA$ $I_b=0$
Emitter-Base Breakdown Voltage	$BV_{ebo}$	8			V	$I_e=100\mu A$ $I_c=0$
Collector Cutoff Current	$I_{cbo}$			10	$\mu A$	$V_{cb}=420V$ $I_e=0$
Emitter Cutoff Current	$I_{ebo}$			10	$\mu A$	$V_{eb}=8V$ $I_c=0$
DC Current Gain	$H_{fe}$	8		40		$V_{ce}=10V$ $I_c=5mA$
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			0.4	V	$I_c=50mA$ $I_b=10mA$
Base-Emitter Saturation Voltage	$V_{be(sat)}$			1	V	$I_c=50mA$ $I_b=10mA$
Current Gain-Bandwidth product	$f_T$	10			MHz	$V_{ce}=10V$ $I_c=10mA$ $f=1MHz$